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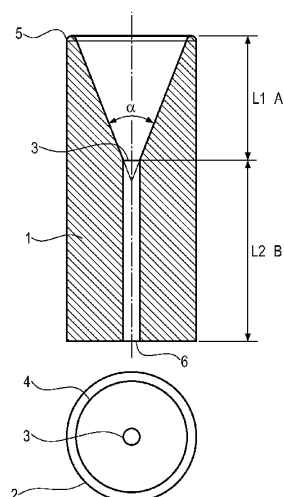
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(54) **Title:** IMPROVED DEVICE FOR DRYING SEMICONDUCTOR SUBSTRATES

Fig. 1



(57) **Abstract:** Device for drying disc-shaped substrates comprising an elongated body (1) having a top surface, a bottom surface and a circumferential surface, comprising a hole in the top surface forming a channel (6) which extends to a lower drainage part (B) of the elongated body and is chamfered having a chamfer depth (L1) and a chamfer angle (α) forming an edge between chamfer and top surface and forming a conical recess suitable for resting a disc shaped substrate, characterized in that the chamfer angle is more than 10° and less than 30° and that the chamfer depth (L1) is more than 6 mm and less than 12 mm.

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